

AMENDMENTS TO THE CLAIMS:

Please accept amendment(s) to the claims as follows:

1. (Currently Amended) A vertical PNP transistor and vertical NPN transistor comprising:
an emitter region of the vertical PNP transistor including silicon and germanium; and
an extrinsic base region of the vertical NPN transistor and an intrinsic base region of the
vertical NPN transistor located in the same layer as the emitter region of the vertical PNP
transistor.

2. (Original) The transistor of claim 1, wherein the germanium makes up no less than 10%
of the silicon and germanium, and wherein the germanium makes up no more than 30% of the
silicon and germanium.

3. (Original) The transistor of claim 1, wherein the silicon is a polysilicon.

4. (Original) The transistor of claim 1, wherein the transistor has a cutoff frequency greater
than 10 GHz.

5. (Original) The transistor of claim 1, wherein the emitter region also includes carbon.

6. (Currently Amended) A vertical ~~Vertical~~ PNP and NPN transistor ~~transistors~~ comprising:
a single layer of silicon that forms an emitter region of the PNP transistor, an extrinsic
base region of the NPN transistor and an intrinsic base region of the NPN transistor.

7. (Currently Amended) The vertical PNP and NPN transistor ~~transistors~~ of claim 6, wherein an emitter region of the PNP transistor includes silicon and germanium.

8. (Currently Amended) The vertical PNP and NPN transistor ~~transistors~~ of claim 7, wherein the germanium makes up no less than 10% of the silicon and germanium, and wherein the germanium makes up no more than 30% of the silicon and germanium.

9. (Currently Amended) The vertical PNP and NPN transistor ~~transistors~~ of claim 7, wherein the emitter region also includes carbon.

10. (Currently Amended) The vertical PNP and NPN transistor ~~transistors~~ of claim 7, wherein the silicon layer is polysilicon in the emitter region of the PNP transistor, and mono-crystal silicon in a portion of the extrinsic base region and mono-crystal silicon in the intrinsic base region of the NPN transistor.

11. (Currently Amended) The vertical PNP and NPN transistor ~~transistors~~ of claim 6, wherein the PNP transistor has a cutoff frequency greater than 10 GHz.

12-20. (Cancelled)